

FEATURES

- DEDICATED THYRISTOR STRUCTURE FOR CAPACITANCE DISCHARGE IGNITION OPERATION
- HIGH PULSE CURRENT CAPABILITY
190A @ $t_p = 10\mu s$
- FAST TURN-ON OPERATION
- DESIGNED FOR HIGH AMBIENT TEMPERATURE (up to 120°C)

BENEFITS

- SPACE SAVING THANKS TO MONOLITHIC FUNCTION INTEGRATION
- HIGH RELIABILITY WITH PLANAR TECHNOLOGY

DESCRIPTION

The FLC01 series has been especially developed for capacitance discharge operation. The main applications are gas lighters or ignitors such as cookers / gas boilers / gas hobs...

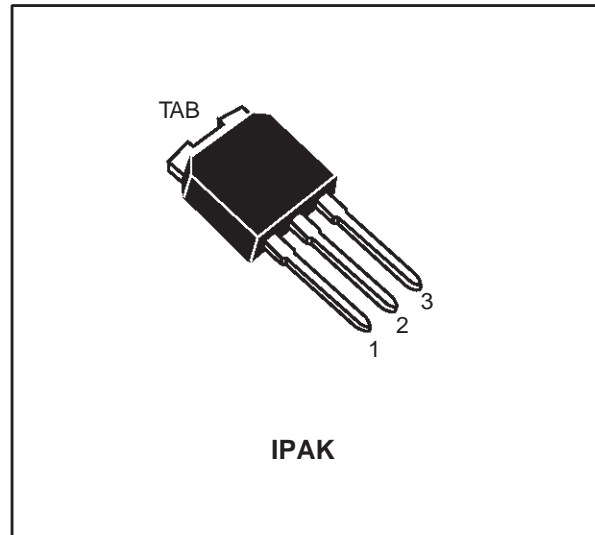
Based on ST's ASDTM technology, it provides a fully integrated function, with high performance and reliability levels, adapted to severe and hot temperature environment.

Th: Thyristor for switching operation.

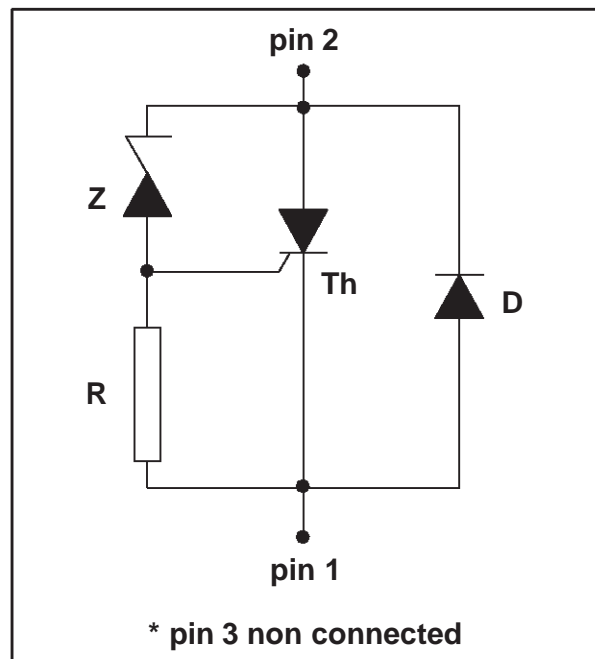
Z: Zener diode to set the threshold voltage.

D: Diode for reverse conduction.

R: 2 kΩ resistor.



FUNCTIONAL DIAGRAM

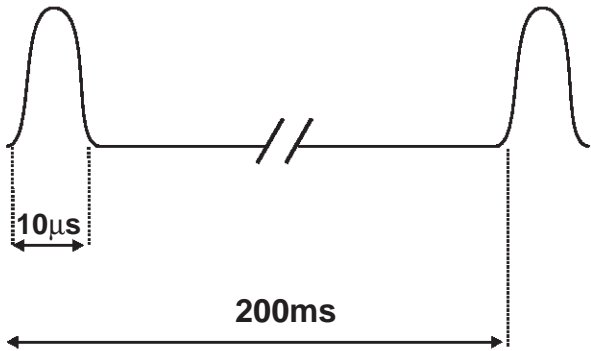


FLC01-200H

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
I _{TRM}	Repetitive surge peak on state current for thyristor -30°C ≤ T _{amb} ≤ 120°C	tp = 10μs (note 1)	190	A
I _{FRM}	Repetitive surge peak on state current for diode -30°C ≤ T _{amb} ≤ 120°C			
di/dt	Critical rate of rise time on state current -30°C ≤ T _{amb} ≤ 120°C		120	A/μs
Tstg T _j	Storage junction temperature range Maximum junction temperature		- 40 to + 150 + 125	°C
Toper	Operating temperature range		-30 + 120	°C
T _L	Maximum lead temperature for soldering during 10s		260	°C

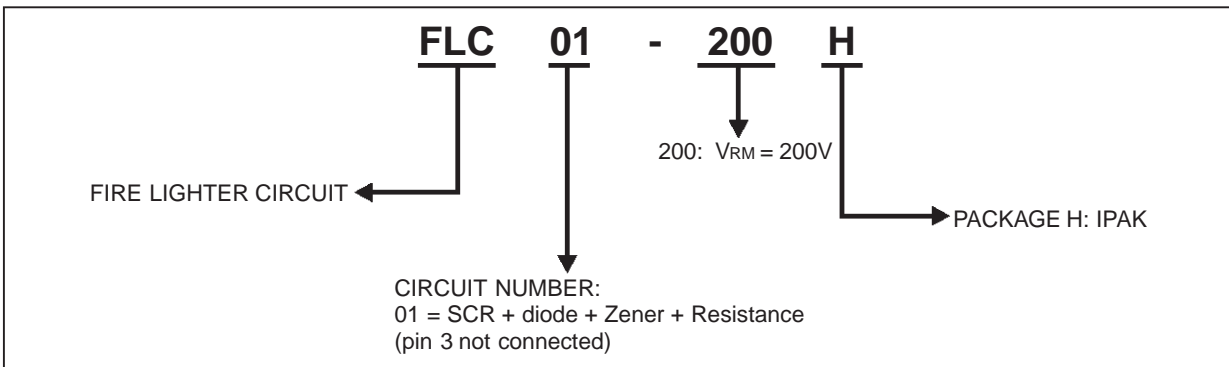
Note 1 : Test current waveform



THERMAL RESISTANCE

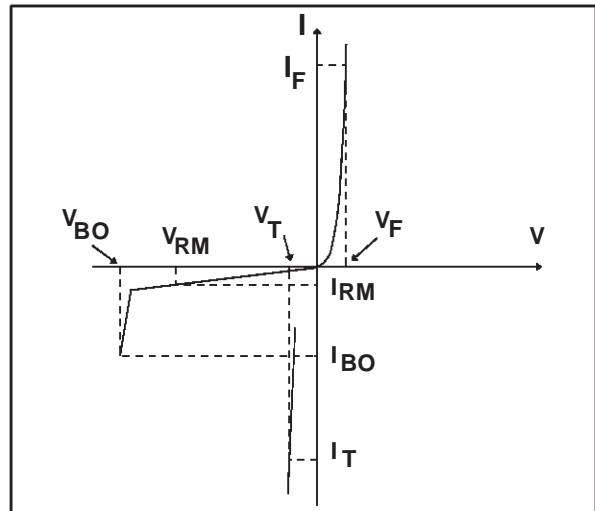
Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Thermal resistance junction to ambient	100	$^{\circ}\text{C/W}$

ORDERING INFORMATION



ELECTRICAL CHARACTERISTICS

Symbol	Parameters
V_{RM}	Stand-off voltage
V_{BO}	Breakover voltage
V_T	On-state voltage
V_F	Diode forward voltage drop
I_{BO}	Breakover current
I_{RM}	Leakage current
αT	Temperature coefficient for V_{BO}



DIODE (D) PARAMETER

Symbol	Test Conditions				Value	Unit
V _F	I _F = 2A	tp ≤ 500μs	Tj = 25°C	Max.	1.7	V

THYRISTOR (Th) and ZENER (Z) PARAMETERS

Symbol	Test conditions		Min.	Typ.	Max.	Unit
I_{RM}	$V_{RM} = 200 V$	$T_j = 25^\circ C$			1	μA
		$T_j = 125^\circ C$			10	μA
V_{BO}	at I_{BO}	$T_j = 25^\circ C$	206	220	233	V
I_{BO}	at V_{BO}	$T_j = 25^\circ C$			0.5	mA
V_T	$I_T = 2A$	$t_p \leq 500\mu s$	$T_j = 25^\circ C$		1.7	V
αT				0.27		$V/^\circ C$

Fig. 1: Relative variation of breakover current versus junction temperature.

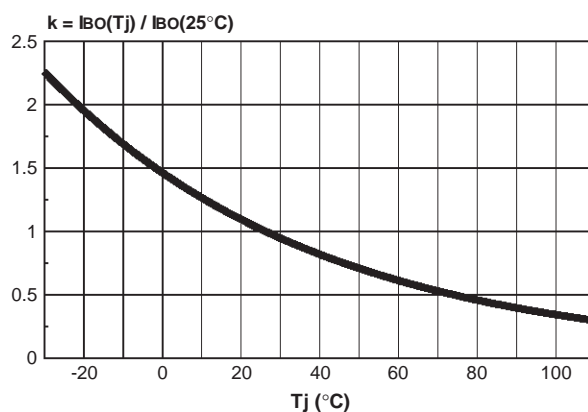
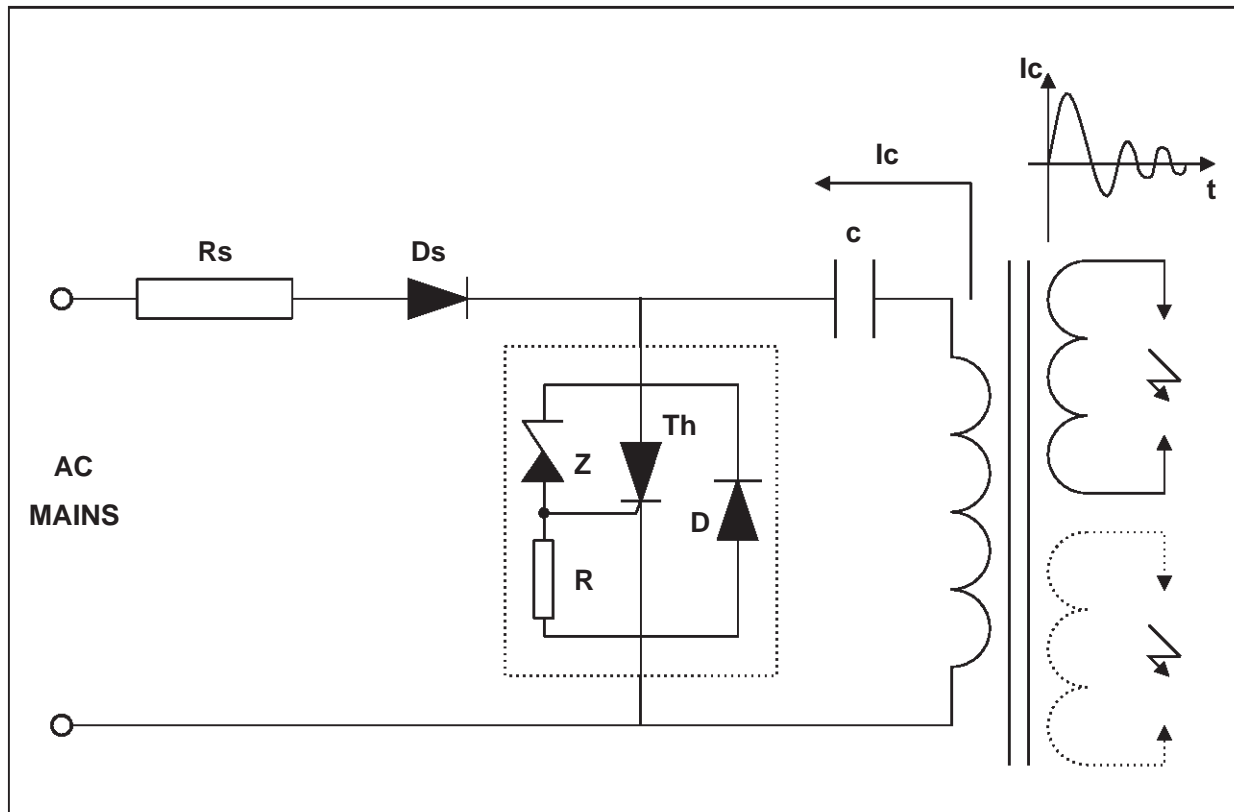


Fig. 2: BASIC APPLICATION



The applications of the lighter using the capacitance discharge topology operate in 2 phases :

PHASE 1

The energy coming from the mains is stored into the capacitor C. For that, the AC voltage is rectified by the diode Ds.

PHASE 2

At the end of the phase 1, the voltage across the capacitor C reaches the avalanche threshold of the zener. Then a current flows through the gate of the thyristor Th which fires.

The firing of the thyristor causes an alternating current to flow through the capacitor C.

The positive parts of this current flow through C, Th and the primary of the HV transformer.

The negative parts of the current flow through C, D and the primary of the HV transformer.

RS RESISTOR CALCULATION

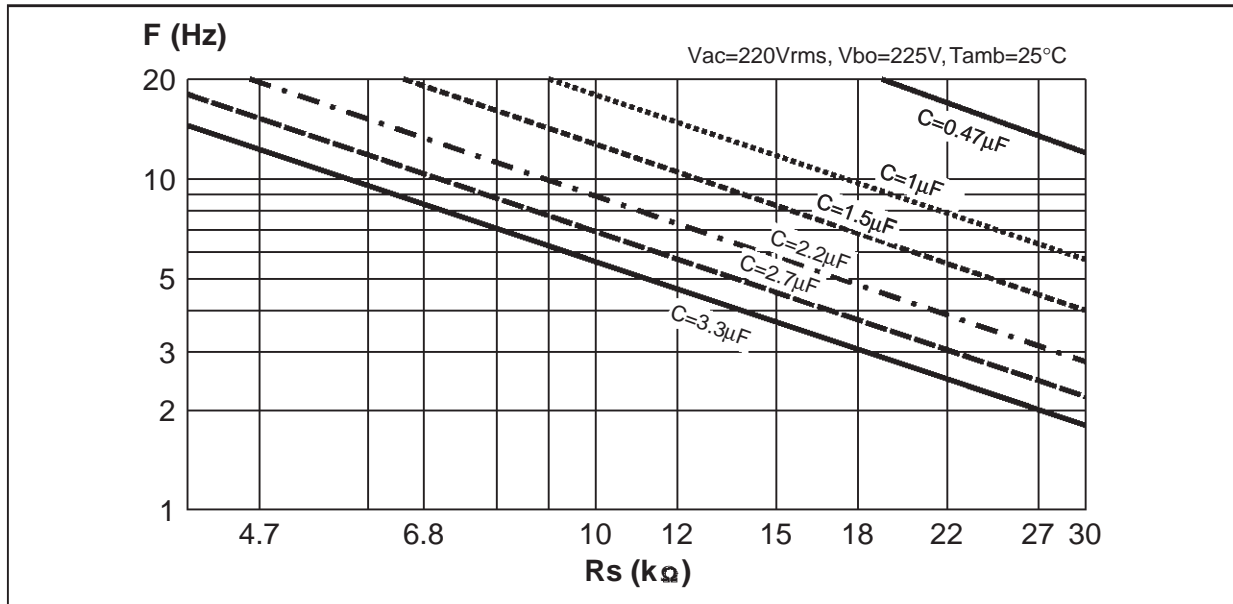
The Rs resistor allows, in addition with the capacitor C, the spark frequency to be adjusted and the current from the mains to be limited. Its value shall allow the thyristor Th to fire even in the worst case. In this case the system must fire with the lower RMS mains voltage value while the breakdown voltage and current of the FLC are at the maximum.

The maximum Rs value is equal to :

$$R_{s \max} = \frac{(V_{AC \min} \cdot \sqrt{2}) - [V_{BO \max} \cdot (1 + \alpha T \cdot (T_{amb} - 25))]}{k \cdot I_{BO}^*}$$

* : see fig 1

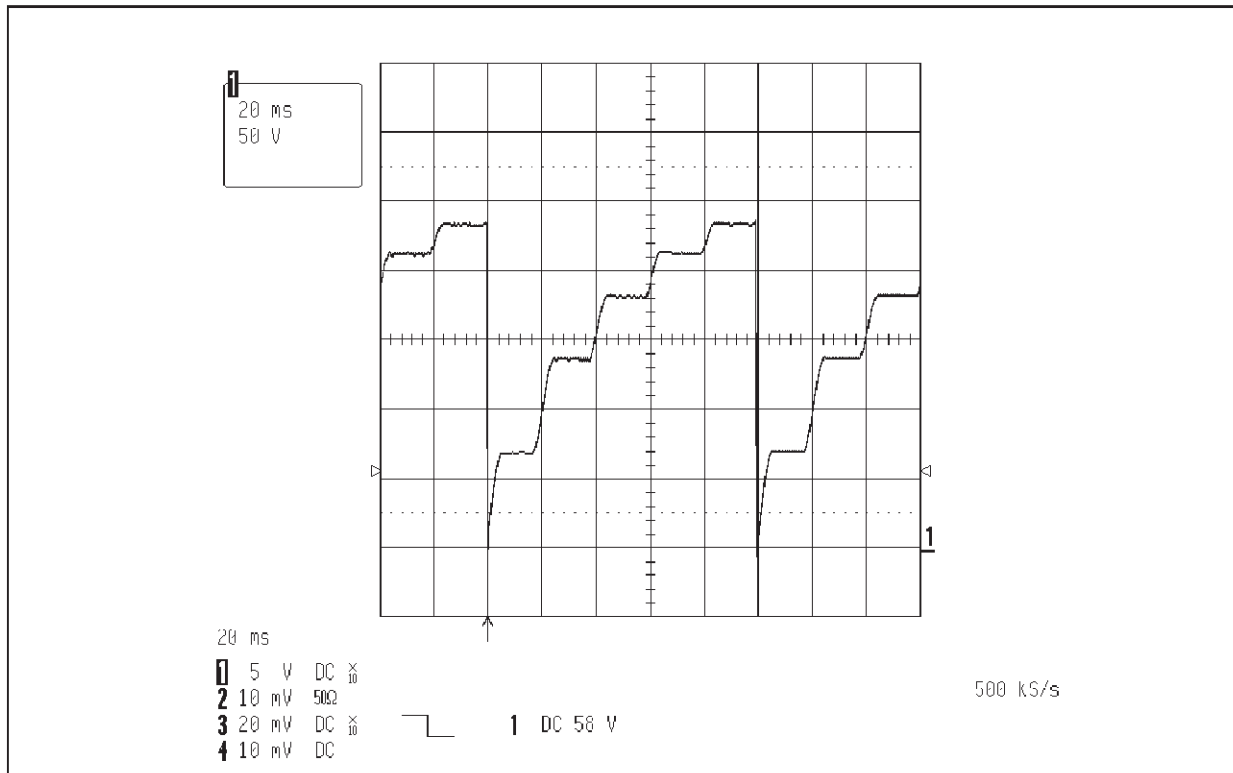
Fig. 3: Spark frequency versus R_s and C



The couple R_s/C can be chosen with the previous curve. Keep in mind the R_s maximum limit for which the system would not work when the AC

mains is minimum. The next curve shows the behavior with $R_s=15k\Omega$ and $C=1\mu F$.

Fig. 4: Voltage across the capacitance with $R_s = 15k\Omega$, $C = 1\mu F$ and $V_{BO} = 225V$.

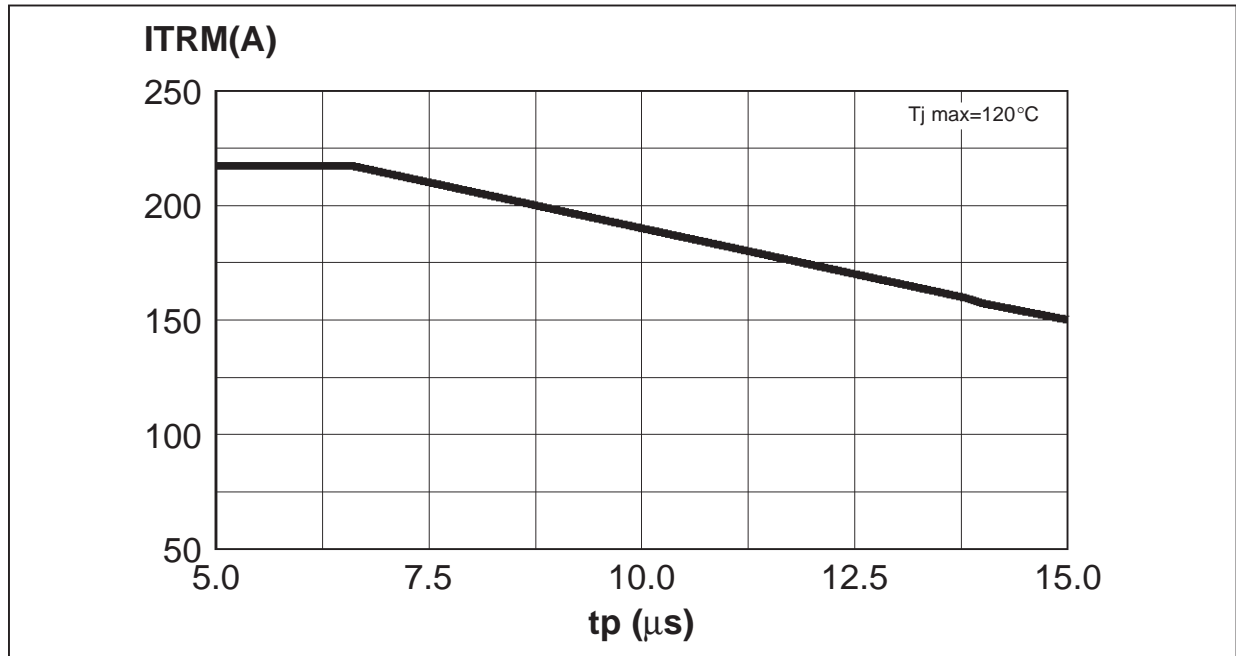


PEAK CURRENT LIMIT

This component is designed to withstand $I_{TRM} = 190A$ for a pulse duration of $10\mu s$ for an

ambient temperature of $120^{\circ}C$ in repetitive surge. The curve of peak current versus the pulse duration allows us to verify if the application is within the FLC operating limit.

Fig. 5: Peak current limit



POWER LOSSES (For $10\mu s$, see note 1)

To evaluate the power losses, please use the following equations :

For the thyristor : $P = 1.18 \times I_{T(AV)} + 0.035 I_{T(RMS)}^2$

For the diode : $P = 0.67 \times I_{F(AV)} + 0.106 I_{F(RMS)}^2$

PACKAGE MECHANICAL DATA

IPAK

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.035	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039
V1		10°			10°	

OTHER INFORMATION

Type	Marking	Package	Weight	Base qty	Delivery mode
FLC01-200H	FLC01-200H	IPAK	0.40 g	75	Tube

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 2000 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia
Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

<http://www.st.com>